## DATA SHEET

# BIPOLAR ANALOG INTEGRATED CIRCUITS $\mu$ PC8106TB, $\mu$ PC8109TB

### SILICON MMIC 2.0 GHz FREQUENCY UP-CONVERTER FOR CELLULAR/CORDLESS TELEPHONES

#### DESCRIPTION

The  $\mu$ PC8106TB and  $\mu$ PC8109TB are silicon monolithic integrated circuit designed as frequency up-converter for cellular/cordless telephone transmitter stage. The  $\mu$ PC8106TB features improved intermodulation and  $\mu$ PC8109TB features low current consumption. From these two version, you can chose either IC corresponding to your system design. These TB suffix ICs which are smaller package than conventional T suffix ICs contribute to reduce your system size.

The  $\mu$ PC8106TB and  $\mu$ PC8109TB are manufactured using NEC's 20 GHz fr NESAT<sup>TM</sup>III silicon bipolar process. This process uses a silicon nitride passivation film and gold electrodes. These materials can protect chip surface from external pollution and prevent corrosion/migration. Thus, this IC has excellent performance, uniformity and reliability.

#### FEATURES

Recommended operating frequency : fRFout = 0.4 GHz to 2.0 GHz, fIFin = 100 MHz to 400 MHz
Supply voltage : Vcc = 2.7 to 5.5 V

•	Supply vollage	. V = 2.7 10 0.0 V
•	High-density surface mounting	: 6-pin super minimold package
•	Low current consumption	: Icc = 9 mA TYP. @ µPC8106TB
		Icc = 5 mA TYP. @ μPC8109TB
•	Minimized carrier leakage	: Due to double balanced mixer
•	Built-in power save function	

#### APPLICATION

• Cellular/cordless telephone up to 2.0 GHz MAX (example: PHS, PDC, DCS1800 and so on)

#### **ORDERING INFORMATION**

Part Number	Markings	Product Type	Package	Supplying Form
μPC8106TB-E3	C2D	High IP₃	6-pin super minimold	Embossed tape 8 mm wide.
μPC8109TB-E3	C2G	Low current consumption	minimoia	Pin 1, 2, 3 face to tape perforation side. QTY 3 kp/Reel.

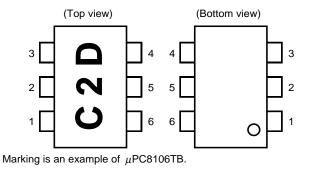
Remark To order evaluation samples, please contact your local NEC sales office.

(Part number for sample order: µPC8106TB, µPC8109TB)

#### Caution Electro-static sensitive devices

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version. Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

#### **PIN CONNECTIONS**



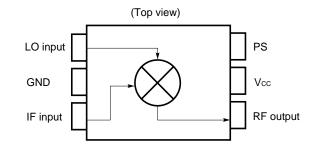
Pin No.	Pin Name
1	IFinput
2	GND
3	LOinput
4	PS
5	Vcc
6	RFoutput

#### ★ SERIES PRODUCTS (TA = +25 °C, VCC = VPS = VRFout = 3.0 V, ZL = ZS = 50 $\Omega$ )

TYPE	PRODUCT NAME	Vcc (V)	Icc (mA)	CG1 (dB)	CG2 (dB)	P <sub>O(sat)</sub> 1 (dBm)	Po <sub>(sat)</sub> 2 (dBm)	OIP₃1 (dBm)	OIP <sub>3</sub> 2 (dBm)
High IP₃	μΡC8106TB	2.7 to 5.5	9	9	7	-2	-4	+5.5	+2.0
Low power consumption	μPC8109TB	2.7 to 5.5	5	6	4	-5.5	-7.5	+1.5	-1.0
Higher IP₃	μ PC8163TB	2.7 to 3.3	16.5	9	5.5	0.5	-2	+9.5	+6

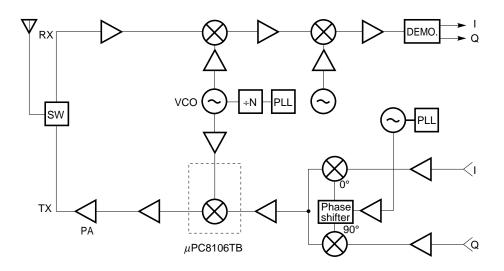
Caution The above table lists the typical performance of each model. See ELECTRICAL CHARACTER-ISTICS for the test conditions.

#### BLOCK DIAGRAM (FOR THE µPC8106TB AND µPC8109TB)

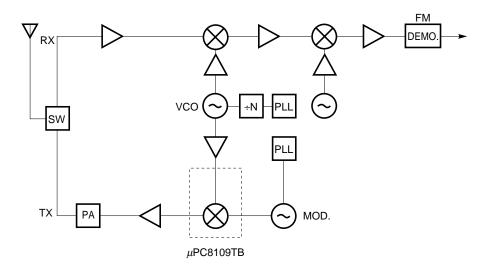


#### SYSTEM APPLICATION EXAMPLES (SCHEMATICS OF IC LOCATION IN THE SYSTEMS)

PHS, DECT



Analog cellular telephone



#### PIN FUNCTIONS (FOR THE $\mu$ PC8106TB AND $\mu$ PC8109TB)

Pin No.	Pin Name	Applied Voltage (V)	Pin Voltage (V) <sup>Note</sup>	Function and Explanation	Equivalent Circuit
1	IFinput	_	1.3	This pin is IF input to double balanced mixer (DBM). The input is designed as high impedance. The circuit contri- butes to suppress spurious signal. Also this symmetrical circuit can keep specified performance insensitive to process-condition distribution. For above reason, double balanced mixer is adopted.	
2	GND	0	_	GND pin. Ground pattern on the board should be formed as wide as possible. Track Length should be kept as short as possible to minimize ground impedance.	
3	LOinput	_	2.4	Local input pin. Recommendable input level is –10 to 0 dBm.	
5	Vcc	2.7 to 5.5	_	Supply voltage pin.	
6	RFoutput	Same bias as Vcc through external inductor	_	This pin is RF output from DBM. This pin is designed as open collector. Due to the high impedance output, this pin should be externally equipped with LC matching circuit to next stage.	
4	PS	Vcc/GND	_	Power save control pin. Bias controls operation as follows.     Pin bias   Control     Vcc   Operation     GND   Power Save	

**Note** Each pin voltage is measured with  $V_{CC} = V_{PS} = V_{RFout} = 3.0 V$ .

#### ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Test Conditions	Rating	Unit
Supply Votage	Vcc	T <sub>A</sub> = +25 °C, Pin 5 and 6	6.0	V
PS pin Input Voltage	Vps	T <sub>A</sub> = +25 °C	6.0	V
Power Dissipation of Package	PD	Mounted on double-sided copper-clad $50 \times 50 \times$ 1.6 mm epoxy glass PWB T <sub>A</sub> = +85 °C	200	mW
Operating Ambient Temperature	TA		-40 to +85	°C
Storage Temperature	T <sub>stg</sub>		-55 to +150	°C
Maximum Input Power	Pin		+10	dBm

#### **RECOMMENDED OPERATING CONDITIONS**

Parameter	Symbol	MIN.	TYP.	MAX.	Unit	Note
Supply Voltage	Vcc	2.7	3.0	5.5	V	The same voltage should be supplied to pin 5 and 6
Operating Ambient Temperature	TA	-40	+25	+85	°C	
Local Input Level	PLOin	-10	-5	0	dBm	$Z_s = 50 \ \Omega$ (without matching)
RF Output Frequency	<b>f</b> RFout	0.4	_	2.0	GHz	With external matching circuit
IF Input Frequency	fıFin	100	-	400	MHz	

#### **ELECTRICAL CHARACTERISTICS**

(TA = +25 °C, Vcc = VRFout = 3.0 V, fIFin = 240 MHz, PLOin = -5 dBm, and VPs  $\ge$  2.7 V unless otherwise specified)

Parameter	Symbol	Conditions	μPC8106TB		μF	Unit			
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.	Unit
Circuit Current	lcc	No signal	4.5	9	13.5	2.5	5	8.0	mA
Circuit Current in Power- save Mode	Icc(PS)	Vps = 0 V	-	-	10	-	-	10	μΑ
Conversion Gain 1	CG1	$f_{RFout} = 0.9 \text{ GHz}, P_{IFin} = -30 \text{ dBm}$	6	9	12	3	6	9	dB
Conversion Gain 2	CG2	f <sub>RFout</sub> = 1.9 GHz, P <sub>IFin</sub> = -30 dBm	4	7	10	1	4	7	dB
Maximum RF Output Power 1	Po(sat)1	$f_{RFout} = 0.9 \text{ GHz}, P_{IFin} = 0 \text{ dBm}$	-4	-2	-	-7.5	-5.5	-	dBm
Maximum RF Output Power 2	Po(sat)2	$f_{RFout} = 1.9 \text{ GHz}, P_{IFin} = 0 \text{ dBm}$	-6.5	-4	-	-10	-7.5	-	dBm

#### OTHER CHARACTERISTICS, FOR REFERENCE PURPOSES ONLY

#### (TA = +25 °C, Vcc = VRFout = 3.0 V, PLOin = -5 dBm, and VPS ≥ 2.7 V unless otherwise mentioned)

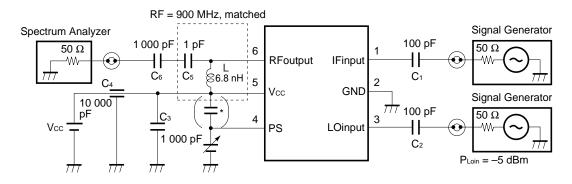
Damage	4	Cumb al	Symbol Conditions			Reference Value	
Parame		Symbol	Condit	IONS	μPC8106TB	μPC8109TB	Unit
Output Third-Order	Distortion	OIP₃1	fIFin1 = 240.0 MHz	frFout = 0.9 GHz	+5.5	+1.5	dBm
Intercept Point		OIP <sub>3</sub> 2	fIFin2 = 240.4 MHz	f <sub>RFout</sub> = 1.9 GHz	+2.0	-1.0	
Third-Order Intermo Distortion 1	Third-Order Intermodulation Distortion 1		fIFint = 240.0 MHz fIFin2 = 240.4 MHz	f <sub>RFout</sub> = 0.9 GHz	-31	-29	dBc
Third-Order Intermo Distortion 2	Third-Order Intermodulation Distortion 2		PıFin = −20 dBm	frefout = 1.9 GHz	-30	-28	dBc
SSB Noise Figure		SSBNF	frFout = 0.9 GHz, fiFin = 240 MHz		8.5	8.5	dB
Power Save Rise time		TPS(rise)	$V_{PS}:\ GND\toV_{CC}$	VPS: $\text{GND} \rightarrow \text{Vcc}$		2.0	μs
Response Time	Fall time	TPS(fall)	$V_{PS} : \ V_{CC} \to GND$		2.0	2.0	μs

# APPLICATION CIRCUIT EXAMPLE CHARACTERSISTICS FOR REFERENCE PURPOSE ONLY (TA = +25 °C, Vcc = VPs = VRFout = 3.0 V, fIFin = 130 MHz, fLoin = 1630 MHz, PLoin = -5 dBm)

Demension	rameter Symbol Conditions		Reference Value	L Incit	
Parameter	Symbol	Conditions	$\mu$ PC8106TB	Unit	
Conversion Gain	CG	f <sub>RFout</sub> = 1.5 GHz, with application circuit example	7	dB	
Maximum RF Output Power	Po(sat)	$f_{RFout} = 1.5 \text{ GHz}$ , with application circuit example	-3.5	dBm	

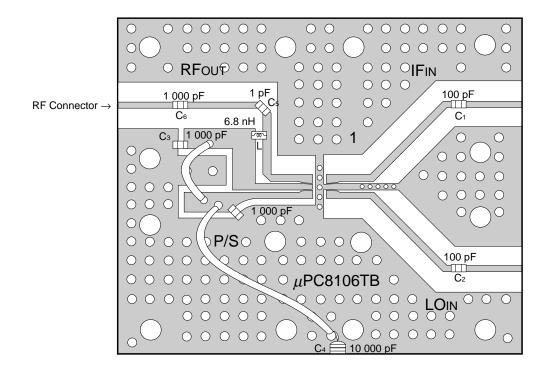
#### **★** TEST CIRCUIT 1 (RF = 900 MHz, for the $\mu$ PC8106TB and $\mu$ PC8109TB)

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\* In case of unstable operation, please connect capacitor 100 pF between 4 pin and 5 pin and adjust the matching circuit.

#### EXAMPLE OF TEST CIRCUIT 1 ASSEMBLED ON EVALUATION BOARD



#### **COMPONENT LIST**

Form	Symbol	Value	
Chip capacitor	C1, C2	100 pF	
	C3, C6	1 000 pF	
	C₅	1 pF	
Through capacitor	C4	10 000 pF	
Chip inductor	L	6.8 nH <sup>№te</sup>	

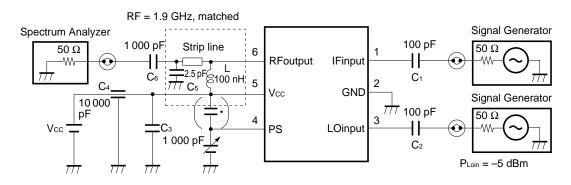
Note 6.8 nH: Murata Mfg. Co., Ltd. LQP31A6N8J04

#### Notes on the board

- 1.  $35 \times 42 \times 0.4$  mm polyimide board, 35  $\mu$ m double-sided copper clad
- 2. Ground pattern on rear of the board
- 3. Solder plated patterns
- **4.** OOO: Through holes
- 5.  $C_6$  is for RF short on the board pattern

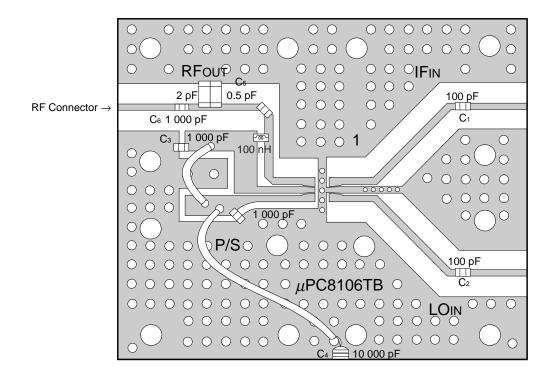
#### **★** TEST CIRCUIT 2 (RF = 1.9 GHz, for the $\mu$ PC8106TB and $\mu$ PC8109TB)

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\* In case of unstable operation, please connect capacitor 100 pF between 4 pin and 5 pin and adjust the matching circuit.

#### EXAMPLE OF TEST CIRCUIT 2 ASSEMBLED ON EVALUATION BOARD



#### **COMPONENT LIST**

Form	Symbol	Value
Chip capacitor	C1, C2	100 pF
	C3, C6	1 000 pF
	C₅	2.5 pF (2.0 pF, 0.5 pF parallel)
Through capacitor	C <sub>4</sub>	10 000 pF
Chip inductor	L	100 nH <sup>Note</sup>

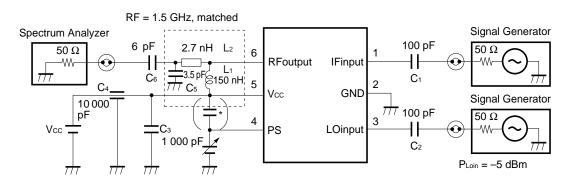
Note 100 nH: Murata Mfg. Co., Ltd. LQN1AR10J(K)04

#### Notes on the board

- 1.  $35 \times 42 \times 0.4$  mm polyimide board, 35  $\mu$ m double-sided copper clad
- 2. Ground pattern on rear of the board
- 3. Solder plated patterns
- **4.** OOO: Through holes

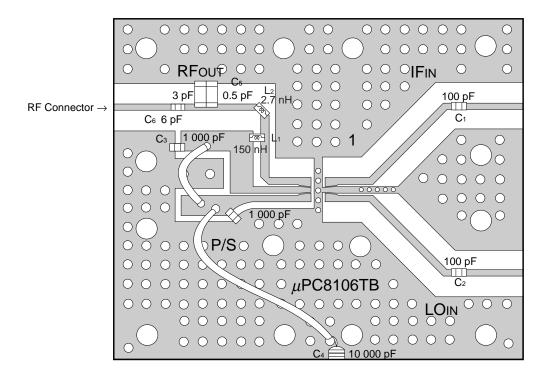
#### **★** APPLICATION CIRCUIT EXAMPLE (RF = 1.5 GHz, for the $\mu$ PC8106TB and $\mu$ PC8109TB)

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\* In case of unstable operation, please connect capacitor 100 pF between 4 pin and 5 pin and adjust the matching circuit.

#### EXAMPLE OF APPLICATION CIRCUIT ASSEMBLED ON EVALUATION BOARD



#### COMPONENT LIST

Form	Symbol	Value	
Chip capacitor	C1, C2	100 pF	
	C <sub>3</sub> 1 000 pF		
	C₅ 3.5 pF (3.0 pF, 0.5 pF paralle		
	C <sub>6</sub>	6 pF	
Through capacitor	C <sub>4</sub>	10 000 pF	
Chip inductor	L1	150 nH <sup>Note 1</sup>	
	L2	2.7 nH <sup>Note 2</sup>	

Notes 1. 150 nH: TOKO Co., Ltd. LL2012-FR15 2. 2.7 nH : TOKO Co., Ltd. LL2012-F2N7S

#### Notes on the board

- 1.  $35 \times 42 \times 0.4$  mm polyimide board,  $35 \mu$ m double-sided copper clad
- 2. Ground pattern on rear of the board
- 3. Solder plated patterns
- **4.**  $\bigcirc\bigcirc\bigcirc$ : Through holes

#### NOTICE

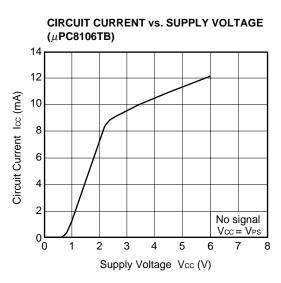
The test circuits and board pattern on data sheet are for performance evaluation use only. (They are not recommended circuits.) In the case of actual design-in, matching circuit should be determined using S parameter of desired frequency in accordance to actual mounting pattern.

For external circuits of the ICs, following Application Note is also available.

• μPC8106, μPC8109 Application Note (Document No. P13683E)

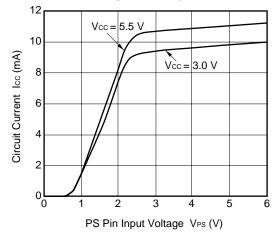
**CIRCUIT CURRENT vs. SUPPLY VOLTAGE** 

# TYPICAL CHARACTERISTICS ( $T_A = +25^{\circ}C$ , $V_{CC} = V_{RFout}$ ) with TEST CIRCUIT 1 or 2, according to the operating frequency, unless otherwise specified

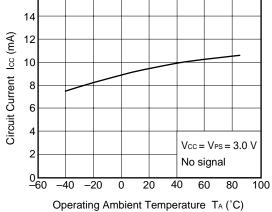


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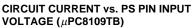


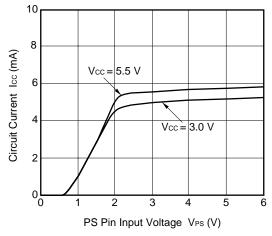


CIRCUIT CURRENT vs. OPERATING AMBIENT TEMPERATURE (µPC8106TB)

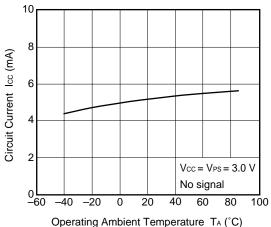


(µPC8109TB) 10 8 Circuit Current Icc (mA) 6 4 2 No signal Vcc = VPs 0⊾ 0 3 4 6 1 2 5 7 8 Supply Voltage Vcc (V)



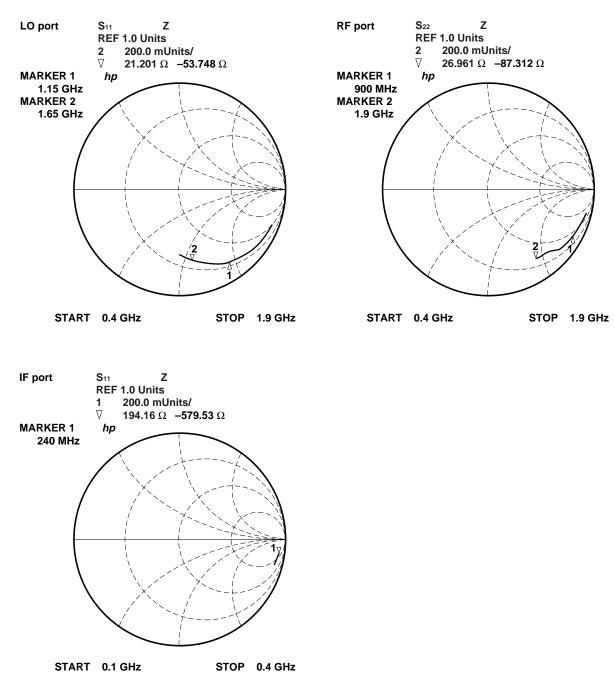


CIRCUIT CURRENT vs. OPERATING AMBIENT TEMPERATURE (µPC8109TB)



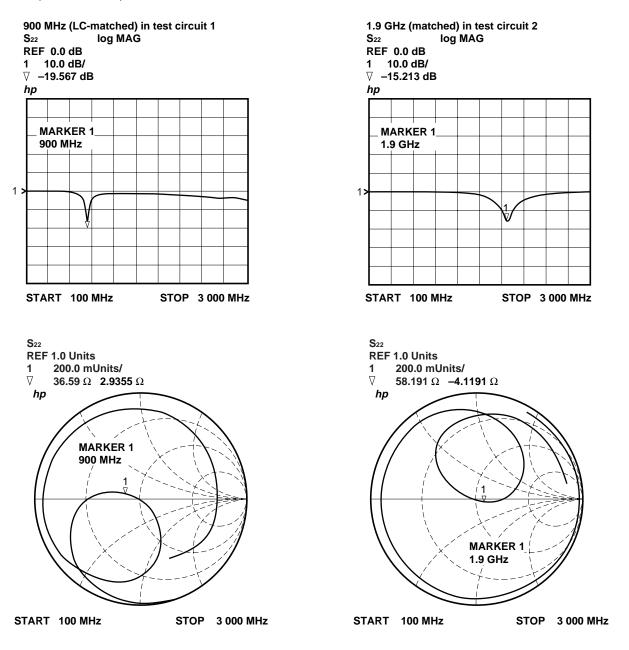
Data Sheet P12770EJ2V0DS00

S-PARAMETERS FOR EACH PORT (Vcc = VPs = VRFout = 3.0 V) –  $\mu$ PC8106TB,  $\mu$ PC8109TB in common – (THE parameters are monitored at DUT pins.)

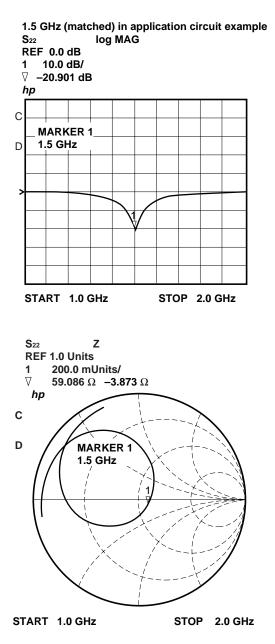


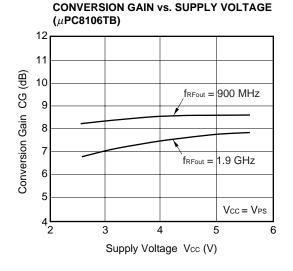
S-PARAMETERS FOR MATCHED RF OUTPUT (Vcc = VPs = VRFout = 3.0 V) – with TEST CIRCUITS 1 and 2 ( $\mu$ PC8106TB,  $\mu$ PC8109TB in common) – (S22 data are monitored at RF connector on board.)

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S-PARAMETERS FOR MATCHED RF OUTPUT ( $Vcc = VPs = V_{RFout} = 3.0 V$ ) – with application circuit example – (S<sub>22</sub> data are monitored at RF connector on board.)





**CONVERSION GAIN vs. LOCAL INPUT LEVEL** 

(µPC8106TB)

fRFout = 900 MHz fLOin = 1140 MHz

Vcc = Vps = 3.0 V

15

12

9

6

3

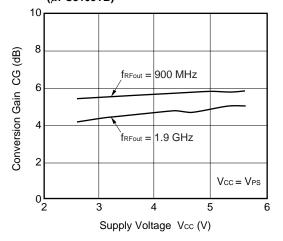
0L -25

-20

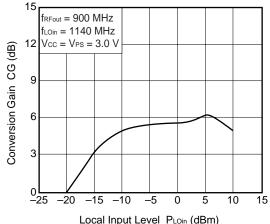
-15 -10

Conversion Gain CG (dB)

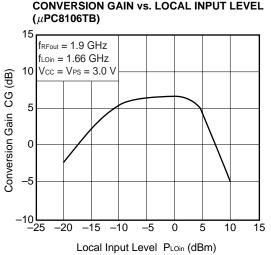
**CONVERSION GAIN vs. SUPPLY VOLTAGE** (µPC8109TB)



**CONVERSION GAIN vs. LOCAL INPUT LEVEL** (µPC8109TB)







**CONVERSION GAIN vs. LOCAL INPUT LEVEL** 

-5 0

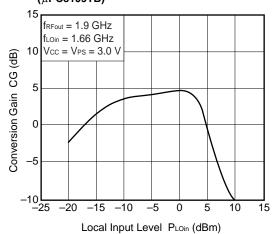
Local Input Level PLOin (dBm)

5

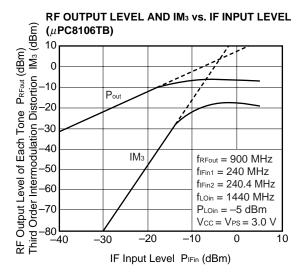
10

15

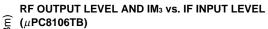
**CONVERSION GAIN vs. LOCAL INPUT LEVEL** (µPC8109TB)

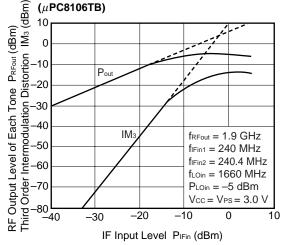


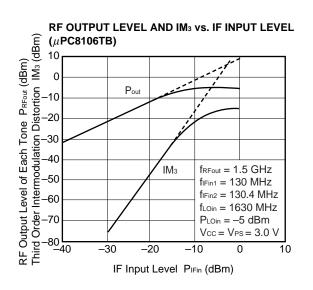
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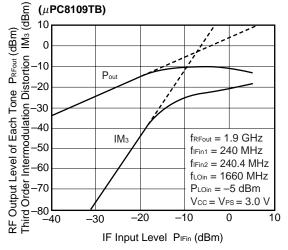


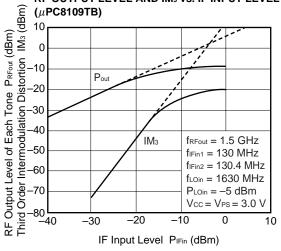


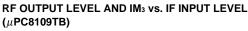


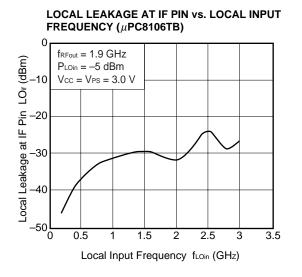
RF OUTPUT LEVEL AND IM<sub>3</sub> vs. IF INPUT LEVEL (µPC8109TB) RF Output Level of Each Tone PRFout (dBm) Pout fRFout = 900 MHz ΙМз  $f_{\text{IFin1}} = 240 \text{ MHz}$ fIFin2 = 240.4 MHz fLOin = 1440 MHz  $P_{LOin} = -5 \, dBm$  $V_{CC} = V_{PS} = 3.0 V$ -30 -20 -100 40 10 IF Input Level PIFin (dBm)



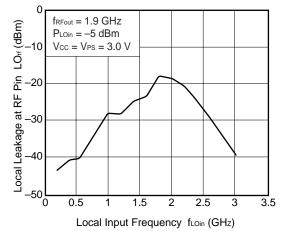








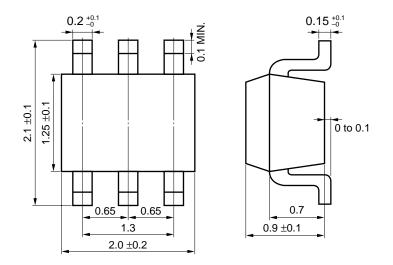
LOCAL LEAKAGE AT RF PIN vs. LOCAL INPUT FREQUENCY ( $\mu$ PC8106TB)



IF LEAKAGE AT RF PIN vs. IF INPUT FREQUENCY (µPC8106TB) 0 fRFout = 1.9 GHz fLOin = 1.66 GHz IF Leakage at RF Pin IFr (dBm) 10  $P_{LOin} = -5 \text{ dBm}$  $f_{IFin} = -30 \text{ dBm}$  $V_{CC} = V_{PS} = 3.0 V$ -20 -30 40 -50L 100 200 300 400 500 600 IF Input Frequency fiFin (MHz)

#### PACKAGE DIMENSIONS

#### 6 pin super minimold (Unit: mm)



#### NOTES ON CORRECT USE

- (1) Observe precutions for handling because of electrostatic sensitive devices.
- (2) Form a ground pattern wide as possible to minimize ground impedance (to prevent undesired oscillation).
- (3) Keep the wiring length of the ground pins as short as possible.
- (4) Connect a bypass capacitor to the Vcc pin.
- (5) Connect a matching circuit to the RF output pin.

#### **RECOMMENDED SOLDERING CONDITIONS**

This product should be soldered under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your NEC sales representative.

Soldering Method	Soldering Conditions	Recommended Condition Symbol
Infrared Reflow	Package peak temperature: 235°C or below Time: 30 seconds or less (at 210°C) Count: 3, Exposure limit: None <sup>Note</sup>	IR35-00-3
VPS	Package peak temperature: 215°C or below Time: 40 seconds or less (at 200°C) Count: 3, Exposure limit: None <sup>Note</sup>	VP15-00-3
Wave Soldering	Soldering bath temperature: 260°C or below Time: 10 seconds or less Count: 1, Exposure limit: None <sup>Note</sup>	WS60-00-1
Partial Heating	Pin temperature: 300°C Time: 3 seconds or less (per side of device) Exposure limit: None <sup>№ee</sup>	-

Note After opening the dry pack, keep it in a place below 25°C and 65% RH for the allowable storage period.

#### Caution Do not use different soldering methods together (except for partial heating).

For details of recommended soldering conditions for surface mounting, refer to information document SEMICONDUCTOR DEVICE MOUNTING TECHNOLOGY MANUAL (C10535E).

[MEMO]

[MEMO]



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- NEC devices are classified into the following three quality grades:

"Standard", "Special", and "Specific". The Specific quality grade applies only to devices developed based on a customer designated "quality assurance program" for a specific application. The recommended applications of a device depend on its quality grade, as indicated below. Customers must check the quality grade of each device before using it in a particular application.

- Standard: Computers, office equipment, communications equipment, test and measurement equipment, audio and visual equipment, home electronic appliances, machine tools, personal electronic equipment and industrial robots
- Special: Transportation equipment (automobiles, trains, ships, etc.), traffic control systems, anti-disaster systems, anti-crime systems, safety equipment and medical equipment (not specifically designed for life support)
- Specific: Aircraft, aerospace equipment, submersible repeaters, nuclear reactor control systems, life support systems or medical equipment for life support, etc.

The quality grade of NEC devices is "Standard" unless otherwise specified in NEC's Data Sheets or Data Books. If customers intend to use NEC devices for applications other than those specified for Standard quality grade, they should contact an NEC sales representative in advance.